

β -Ga₂O₃ epi-wafer for developing planar SBD

Epi-layer

Items	Specifications
Dopant	Si+Cl ^{*1} (n-type)
Doping concentration	The mid to late order of 10 ¹⁵ cm ⁻³
Thickness	15 μ m

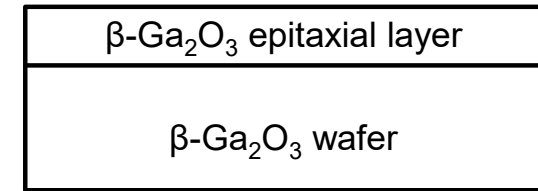
*1: Unintentionally-doped

Wafer

Items	Specifications
Dopant	Sn (n-type)
Resistivity	0.007–0.042 $\Omega \cdot \text{cm}$
Orientation	(001)
Size	2 inch, 100 mm
Backside finish	CMP
Thickness	650 μ m
XRD FWHM	≤ 50 arcsec

Remarks

- 1 There are cases in which the other side of OF is chipped (a maximum of around IF width).
- 2 These products must be used for research and development purposes only.
- 3 The substrates must not be used as a seed crystal.
- 4 The specifications are subject to change without notice.



Cross section of β -Ga₂O₃ epitaxial wafer

